

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

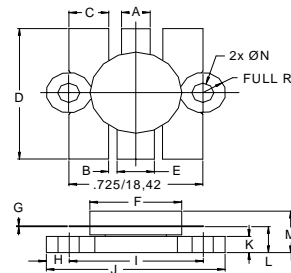
The **ASI TVV030** is Designed for Television Band III Applications up to 225 MHz.

FEATURES:

- Common Emitter
- $P_G = 6.0$ dB at 30 W/225 MHz
- **Omnigold™** Metalization System
- Emitter Ballasting

MAXIMUM RATINGS

I_C	14 A
V_{CB0}	45 V
V_{CEO}	25 V
V_{EBO}	4.0 V
P_{DISS}	146 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.2 °C/W

PACKAGE STYLE .500 6L FLG


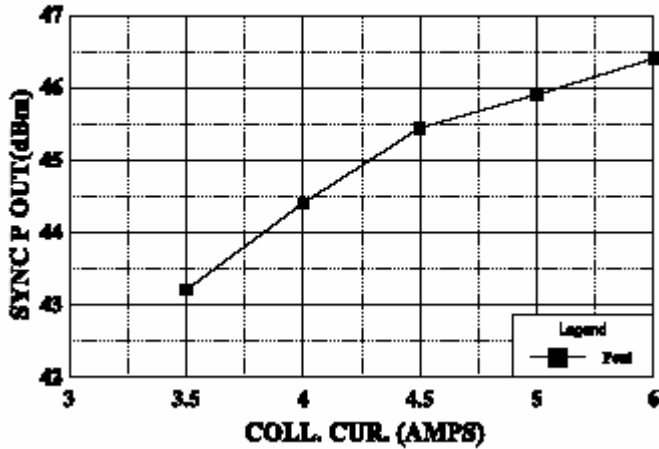
DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B		.045 / 1.14
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H		.125 / 3.18
I		.725 / 18.42
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M		.285 / 7.24
N	.120 / 3.05	.135 / 3.43

ORDER CODE: ASI10660
CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 100$ mA $R_{BE} = 10 \Omega$	45			V
BV_{CEO}	$I_C = 25$ mA	25			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ mA	10	40		---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz		135		pF
P_G	$V_{CE} = 25$ V $I_C = 5.0$ A $f = 175$ -225 MHz	6.0	7.0		dB
IMD_1	$P_{OUT} = 30$ W		-50		dBc
VSWR				3:1	---

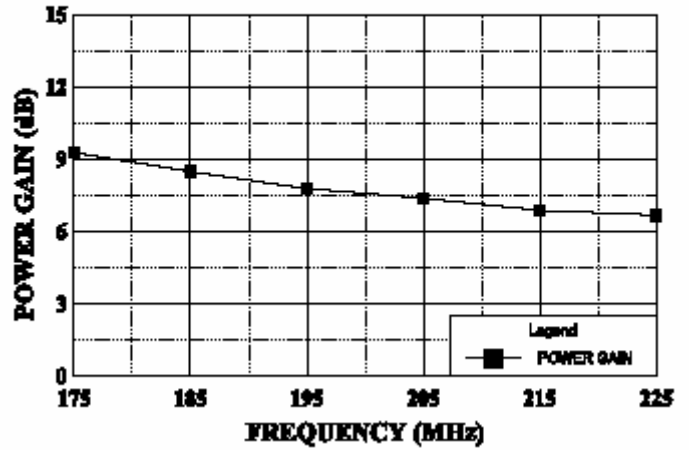
SYNC OUTPUT vs COLLECTOR CURRENT

Vcc = 25V, Frequency 225 MHz



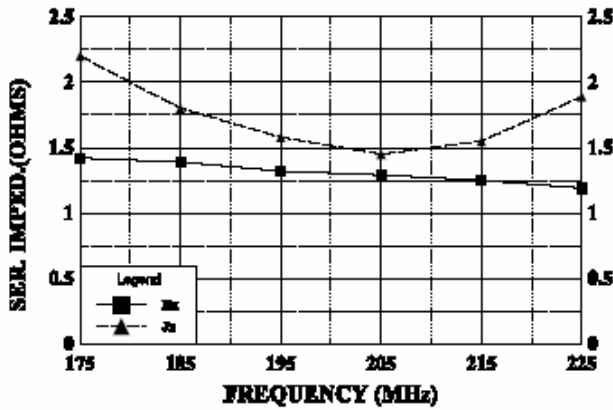
POWER GAIN vs FREQUENCY

Vcc = 25V, Ic = 5.0A, Tbs = 65 C



SERIES INPUT IMPEDANCE vs FREQUENCY

Vcc = 25V, Is = 5.00A, Tbs = 65 C



SERIES LOAD IMPEDANCE vs FREQUENCY

Vcc = 25V, Ic = 5.0A, Tbs = 65 C

